

IS61SF25632T/D IS61LF25632T/D
IS61SF25636T/D IS61LF25636T/D
IS61SF51218T/D IS61LF51218T/D



256K x 32, 256K x 36, 512K x 18
SYNCHRONOUS FLOW-THROUGH
STATIC RAM

FEBRUARY 2002

FEATURES

- Internal self-timed write cycle
- Individual Byte Write Control and Global Write
- Clock controlled, registered address, data and control
- Pentium™ or linear burst sequence control using MODE input
- Three chip enable option for simple depth expansion and address pipelining
- Common data inputs and data outputs
- JEDEC 100-Pin TQFP and 119-pin PBGA package
- Single +3.3V, +10%, -5% power supply
- Power-down snooze mode
- 3.3V I/O for SF
- 2.5V I/O for LF
- Snooze MODE for reduced-power standby
- T version (three chip selects)
- D version (two chip selects)

DESCRIPTION

The *ISSI* IS61SF25632, IS61SF25636, IS61SF51218, IS61LF25632, IS61LF25636, and IS61LF51218 are high-speed, low-power synchronous static RAMs designed to provide a burstable, high-performance, secondary cache for the Pentium™, 680X0™, and PowerPC™ microprocessors. The IS61SF25632 and IS61LF25632 are organized as 262,144 words by 32 bits and the IS61SF25636 and IS61LF25636 are organized as 262,144 words by 36 bits. The IS61SF51218 and IS61LF51218 are organized as 524,288 words by 18 bits. Fabricated with *ISSI*'s advanced CMOS technology, the device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit. All synchronous inputs pass through registers that are controlled by a positive-edge-triggered single clock input.

Write cycles are internally self-timed and are initiated by the rising edge of the clock input. Write cycles can be from one to four bytes wide as controlled by the write control inputs.

Separate byte enables allow individual bytes to be written. Byte write operation is performed by using byte write enable (BWE).input combined with one or more individual byte write signals (BWx). In addition, Global Write (GW) is available for writing all bytes at one time, regardless of the byte write controls.

Bursts can be initiated with either \overline{ADSP} (Address Status Processor) or \overline{ADSC} (Address Status Cache Controller) input pins. Subsequent burst addresses can be generated internally and controlled by the \overline{ADV} (burst address advance) input pin.

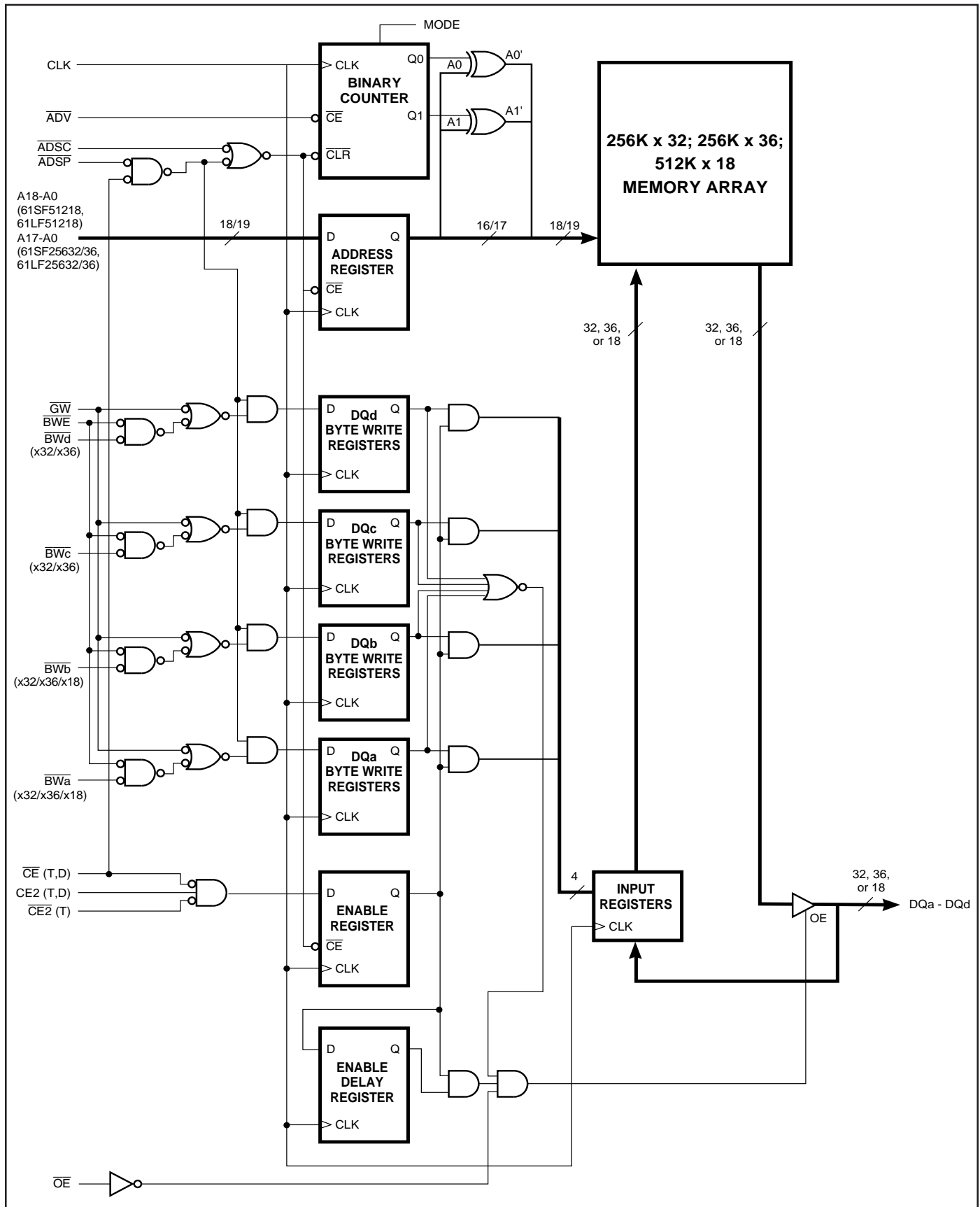
The mode pin is used to select the burst sequence order, Linear burst is achieved when this pin is tied LOW. Interleave burst is achieved when this pin is tied HIGH or left floating.

FAST ACCESS TIME

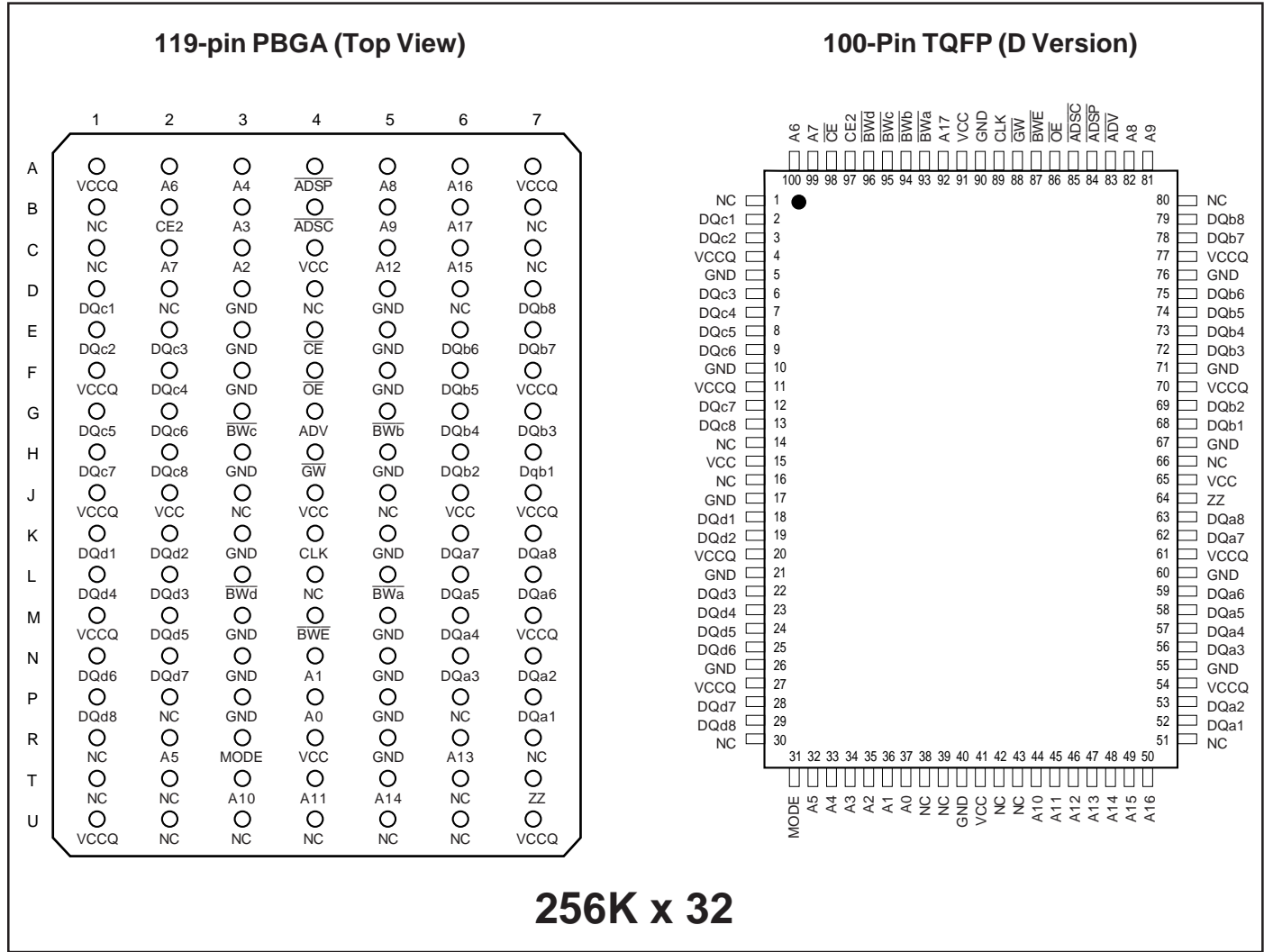
| Symbol | Parameter | -8.5 | -9 | -10 | Units |
|--------|-------------------|------|----|-----|-------|
| tkQ | Clock Access Time | 8.5 | 9 | 10 | ns |
| tkC | Cycle Time | 11 | 15 | 15 | ns |
| | Frequency | 90 | 66 | 66 | MHz |

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BLOCK DIAGRAM



PIN CONFIGURATION

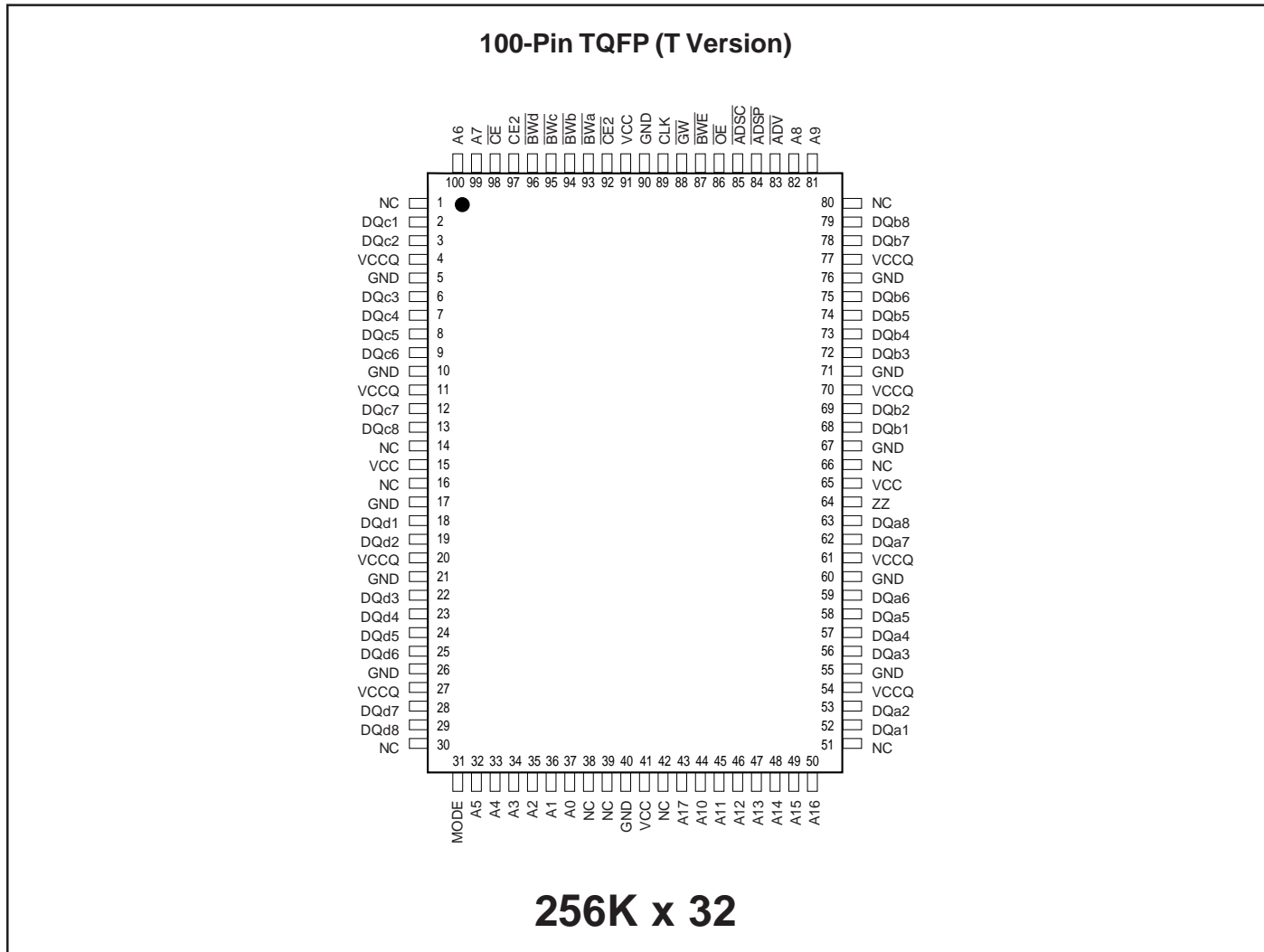


PIN DESCRIPTIONS

| | |
|----------------------------------|---|
| A0, A1 | Synchronous Address Inputs. These pins must be tied to the two LSBs of the address bus. |
| A2-A17 | Synchronous Address Inputs |
| CLK | Synchronous Clock |
| ADSP | Synchronous Processor Address Status |
| ADSC | Synchronous Controller Address Status |
| ADV | Synchronous Burst Address Advance |
| BW _a -BW _d | Synchronous Byte Write Enable |
| BWE | Synchronous Byte Write Enable |

| | |
|----------------------------------|--|
| GW | Synchronous Global Write Enable |
| CE, CE2 | Synchronous Chip Enable |
| OE | Output Enable |
| DQ _a -DQ _d | Synchronous Data Input/Output |
| MODE | Burst Sequence Mode Selection |
| V _{cc} | +3.3V Power Supply |
| GND | Ground |
| V _{ccq} | Isolated Output Buffer Supply: +3.3V or 2.5V |
| ZZ | Snooze Enable |

PIN CONFIGURATION

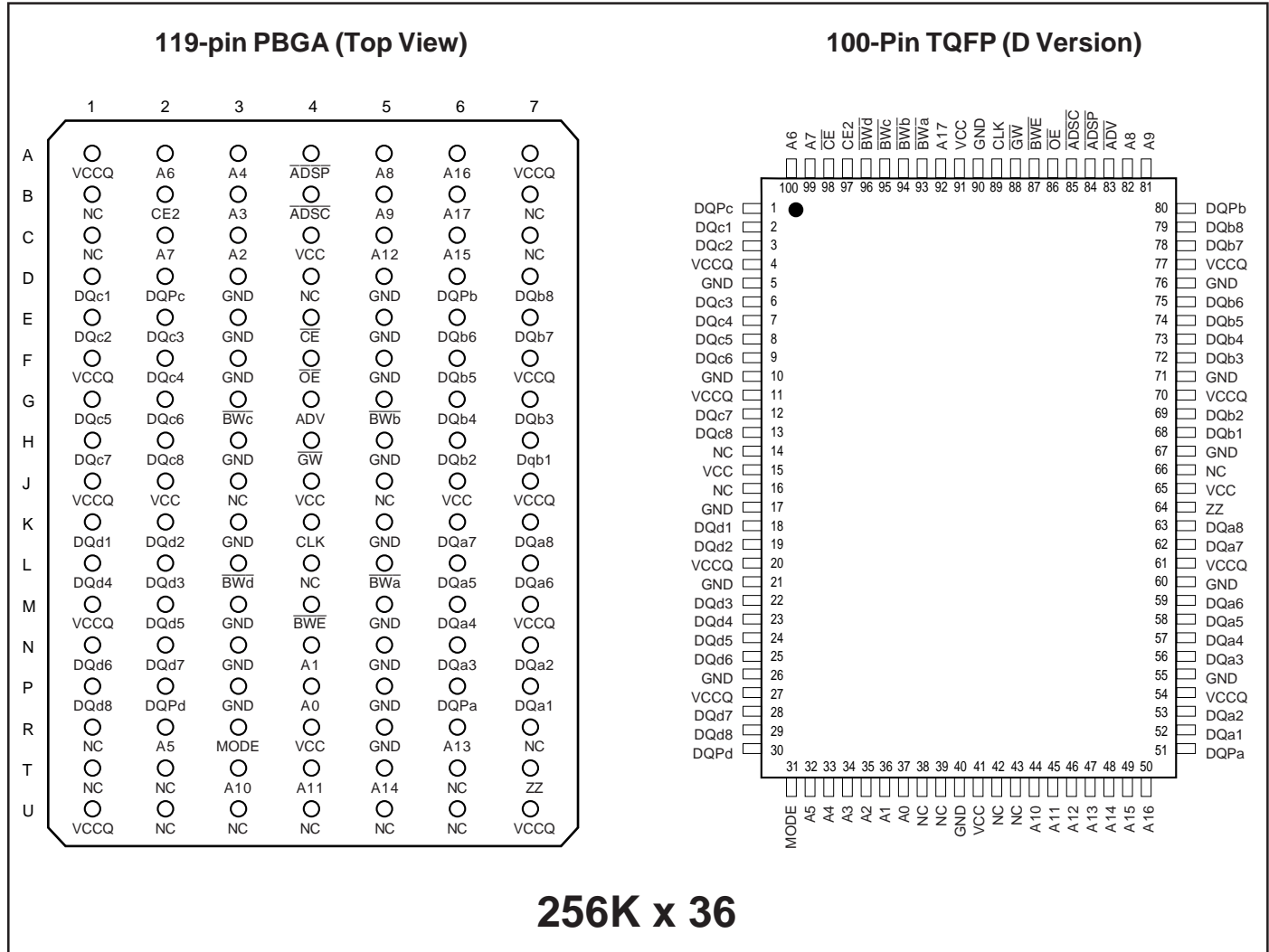


PIN DESCRIPTIONS

| | |
|-------------------|---|
| A0, A1 | Synchronous Address Inputs. These pins must be tied to the two LSBs of the address bus. |
| A2-A17 | Synchronous Address Inputs |
| CLK | Synchronous Clock |
| ADSP | Synchronous Processor Address Status |
| ADSC | Synchronous Controller Address Status |
| ADV | Synchronous Burst Address Advance |
| BW \bar{a} -BWD | Synchronous Byte Write Enable |
| BWE | Synchronous Byte Write Enable |

| | |
|--------------------------------|---|
| $\bar{G}W$ | Synchronous Global Write Enable |
| $\bar{C}E$, $\bar{C}E2$, CE2 | Synchronous Chip Enable |
| $\bar{O}E$ | Output Enable |
| DQa-DQd | Synchronous Data Input/Output |
| MODE | Burst Sequence Mode Selection |
| Vcc | +3.3V Power Supply |
| GND | Ground |
| Vccq | Isolated Output Buffer Supply: +3.3V or 2.5V |
| ZZ | Snooze Enable |

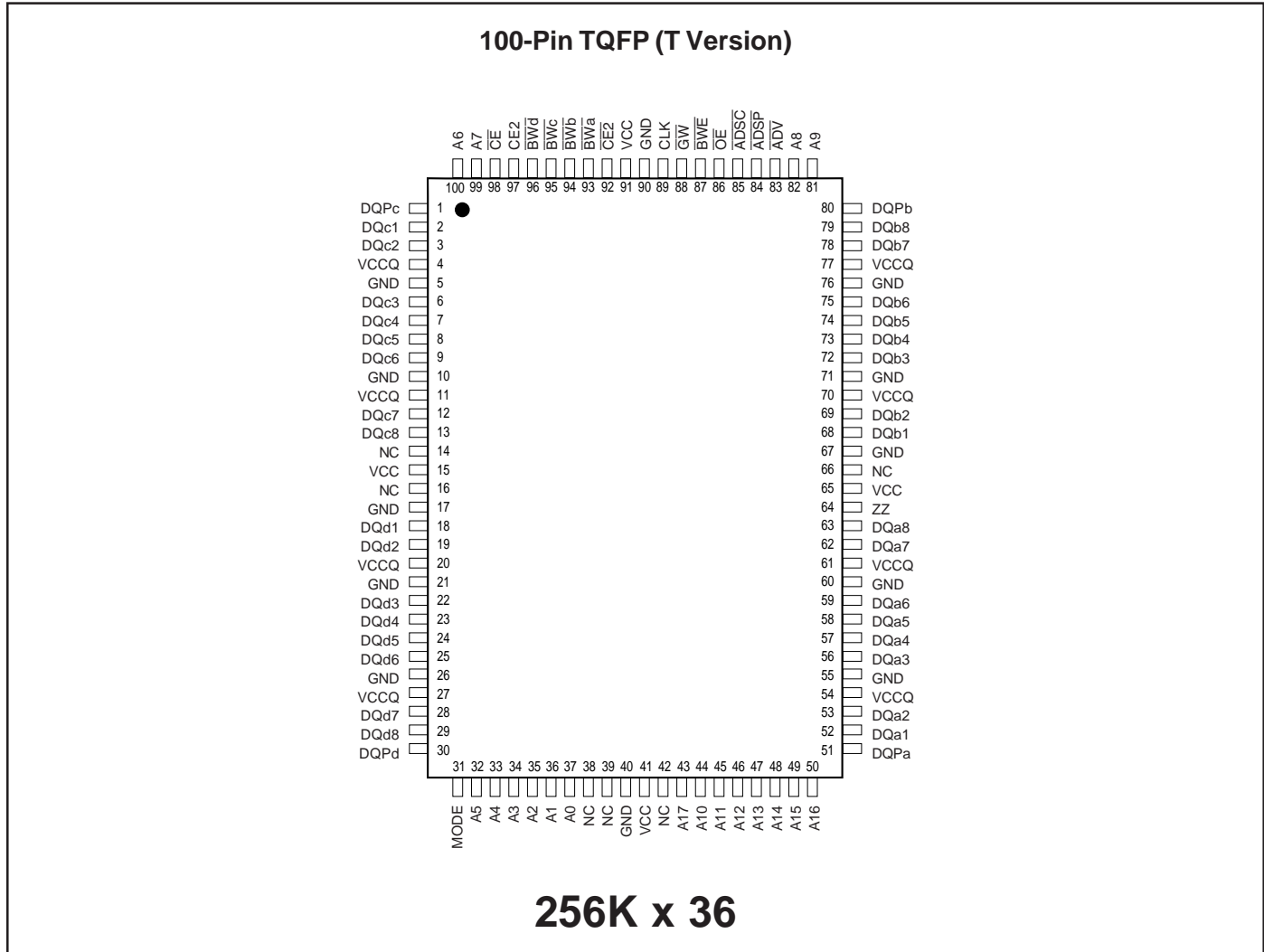
PIN CONFIGURATION



PIN DESCRIPTIONS

| | | | |
|-------------------------------------|--|-----------------------|---|
| A0, A1 | Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus. | \overline{GW} | Synchronous Global Write Enable |
| A2-A17 | Synchronous Address Inputs | \overline{CE} , CE2 | Synchronous Chip Enable |
| CLK | Synchronous Clock | \overline{OE} | Output Enable |
| \overline{ADSP} | Synchronous Processor Address Status | DQa-DQd | Synchronous Data Input/Output |
| \overline{ADSC} | Synchronous Controller Address Status | MODE | Burst Sequence Mode Selection |
| \overline{ADV} | Synchronous Burst Address Advance | Vcc | +3.3V Power Supply |
| \overline{BWA} - \overline{BWD} | Synchronous Byte Write Enable | GND | Ground |
| \overline{BWE} | Synchronous Byte Write Enable | Vccq | Isolated Output Buffer Supply: +3.3V or 2.5V |
| | | ZZ | Snooze Enable |
| | | DQPa-DQPd | Parity Data I/O |

PIN CONFIGURATION

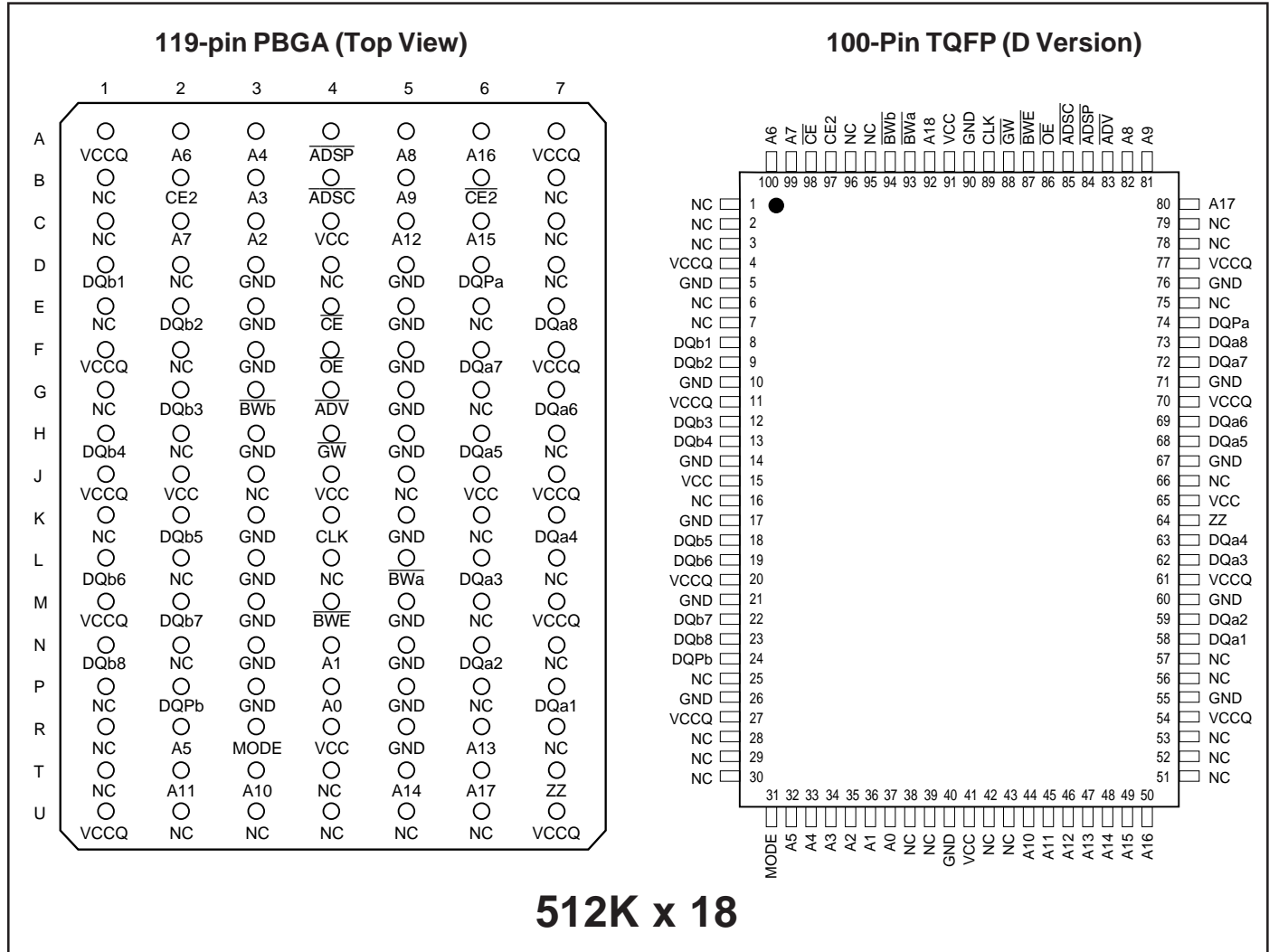


PIN DESCRIPTIONS

| | |
|---|---|
| A0, A1 | Synchronous Address Inputs. These pins must be tied to the two LSBs of the address bus. |
| A2-A17 | Synchronous Address Inputs |
| CLK | Synchronous Clock |
| $\overline{\text{ADSP}}$ | Synchronous Processor Address Status |
| $\overline{\text{ADSC}}$ | Synchronous Controller Address Status |
| ADV | Synchronous Burst Address Advance |
| $\overline{\text{BwA}}-\overline{\text{BwD}}$ | Synchronous Byte Write Enable |
| $\overline{\text{BwE}}$ | Synchronous Byte Write Enable |

| | |
|---|---|
| $\overline{\text{GW}}$ | Synchronous Global Write Enable |
| $\overline{\text{CE}}, \overline{\text{CE2}}, \text{CE2}$ | Synchronous Chip Enable |
| $\overline{\text{OE}}$ | Output Enable |
| DQa-DQd | Synchronous Data Input/Output |
| MODE | Burst Sequence Mode Selection |
| Vcc | +3.3V Power Supply |
| GND | Ground |
| Vccq | Isolated Output Buffer Supply: +3.3V or 2.5V |
| ZZ | Snooze Enable |
| DQPa-DQPd | Parity Data I/O |

PIN CONFIGURATION

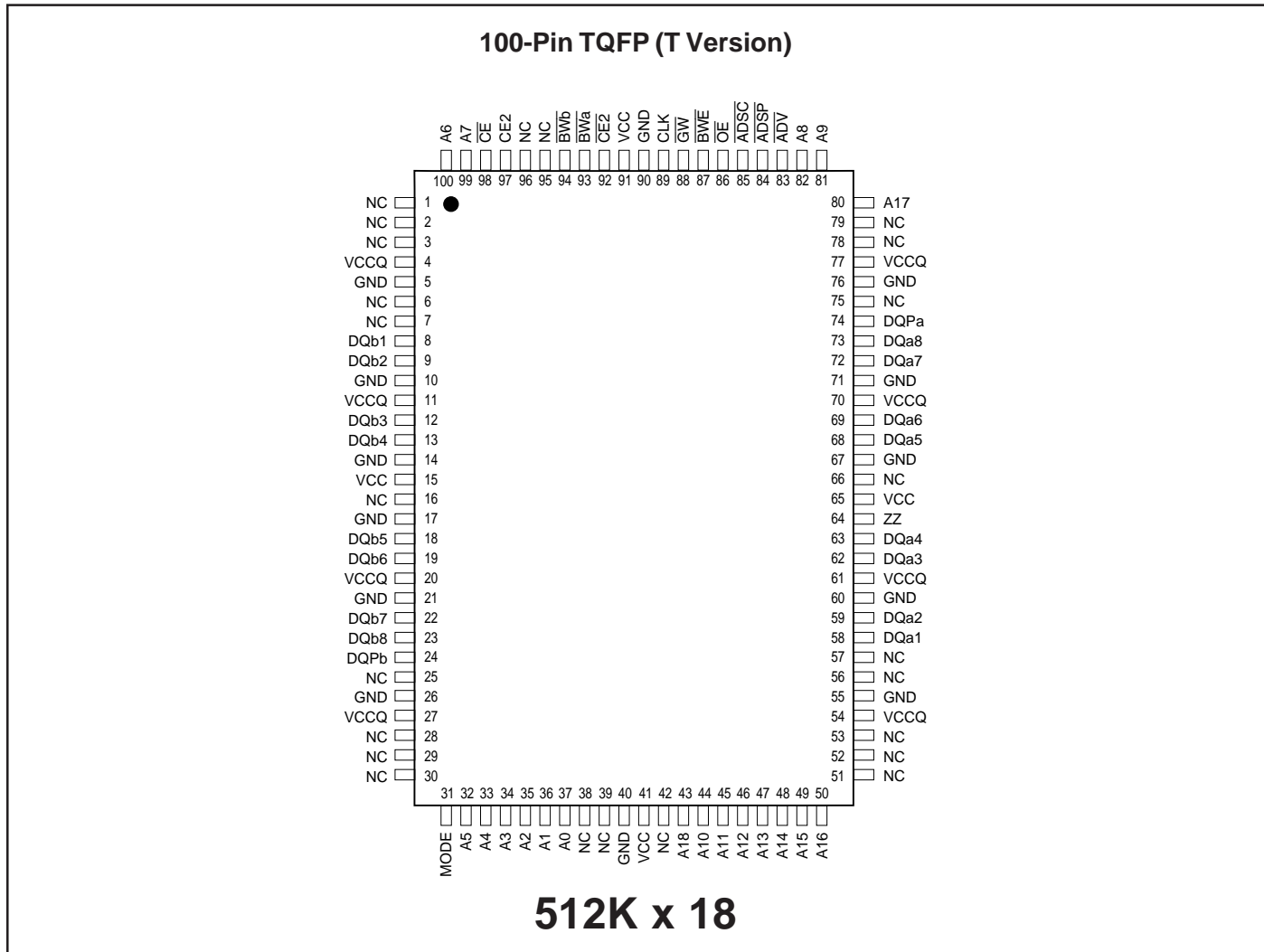


512K x 18

PIN DESCRIPTIONS

| | | | |
|----------------------|--|-----------------------|--|
| A0, A1 | Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus. | \overline{GW} | Synchronous Global Write Enable |
| A2-A18 | Synchronous Address Inputs | \overline{CE} , CE2 | Synchronous Chip Enable |
| CLK | Synchronous Clock | \overline{OE} | Output Enable |
| \overline{ADSP} | Synchronous Processor Address Status | DQa-DQb | Synchronous Data Input/Output |
| \overline{ADSC} | Synchronous Controller Address Status | MODE | Burst Sequence Mode Selection |
| \overline{ADV} | Synchronous Burst Address Advance | Vcc | +3.3V Power Supply |
| $\overline{BWA-BWb}$ | Synchronous Byte Write Enable | GND | Ground |
| \overline{BWE} | Synchronous Byte Write Enable | Vccq | Isolated Output Buffer Supply: 3.3V or 2.5V |
| | | ZZ | Snooze Enable |
| | | DQPa-DQPb | Parity Data I/O DQPa is parity for DQa1-a8; DQPb is parity for DQb1-b8 |

PIN CONFIGURATION



PIN DESCRIPTIONS

| | | | |
|----------------------|--|---|--|
| A0, A1 | Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus. | \overline{GW} | Synchronous Global Write Enable |
| A2-A18 | Synchronous Address Inputs | $\overline{CE}, \overline{CE2}, \overline{CE2}$ | Synchronous Chip Enable |
| CLK | Synchronous Clock | \overline{OE} | Output Enable |
| \overline{ADSP} | Synchronous Processor Address Status | DQa-DQb | Synchronous Data Input/Output |
| \overline{ADSC} | Synchronous Controller Address Status | MODE | Burst Sequence Mode Selection |
| ADV | Synchronous Burst Address Advance | Vcc | +3.3V Power Supply |
| $\overline{BWA-BWb}$ | Synchronous Byte Write Enable | GND | Ground |
| \overline{BWE} | Synchronous Byte Write Enable | Vccq | Isolated Output Buffer Supply: 3.3V or 2.5V |
| | | ZZ | Snooze Enable |
| | | DQPa-DQPb | Parity Data I/O DQPa is parity for DQa1-a8; DQPb is parity for DQb1-b8 |

TRUTH TABLE

| Operation | Address | | | | | | | | | |
|-----------------------------|----------|-----------------|-----|------------------|-------------------|-------------------|------------------|--------------------|-----------------|--------|
| | Used | \overline{CE} | CE2 | $\overline{CE2}$ | \overline{ADSP} | \overline{ADSC} | \overline{ADV} | \overline{WRITE} | \overline{OE} | DQ |
| Deselected, Power-down | None | H | X | X | X | L | X | X | X | High-Z |
| Deselected, Power-down | None | L | X | H | L | X | X | X | X | High-Z |
| Deselected, Power-down | None | L | L | X | L | X | X | X | X | High-Z |
| Deselected, Power-down | None | L | X | H | H | L | X | X | X | High-Z |
| Deselected, Power-down | None | L | L | X | H | L | X | X | X | High-Z |
| Read Cycle, Begin Burst | External | L | H | L | L | X | X | X | X | Q |
| Read Cycle, Begin Burst | External | L | H | L | H | L | X | Read | X | Q |
| Write Cycle, Begin Burst | External | L | H | L | H | L | X | Write | X | D |
| Read Cycle, Continue Burst | Next | X | X | X | H | H | L | Read | L | Q |
| Read Cycle, Continue Burst | Next | X | X | X | H | H | L | Read | H | High-Z |
| Read Cycle, Continue Burst | Next | H | X | X | X | H | L | Read | L | Q |
| Read Cycle, Continue Burst | Next | H | X | X | X | H | L | Read | H | High-Z |
| Write Cycle, Continue Burst | Next | X | X | X | H | H | L | Write | X | D |
| Write Cycle, Continue Burst | Next | H | X | X | X | H | L | Write | X | D |
| Read Cycle, Suspend Burst | Current | X | X | X | H | H | H | Read | L | Q |
| Read Cycle, Suspend Burst | Current | X | X | X | H | H | H | Read | H | High-Z |
| Read Cycle, Suspend Burst | Current | H | X | X | X | H | H | Read | L | Q |
| Read Cycle, Suspend Burst | Current | H | X | X | X | H | H | Read | H | High-Z |
| Write Cycle, Suspend Burst | Current | X | X | X | H | H | H | Write | X | D |
| Write Cycle, Suspend Burst | Current | H | X | X | X | H | H | Write | X | D |

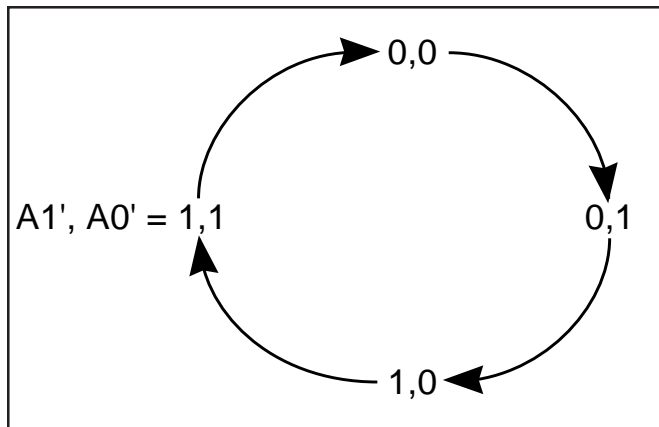
PARTIAL TRUTH TABLE

| Function | \overline{GW} | \overline{BWE} | \overline{Bwa} | \overline{Bwb} | \overline{Bwc} | \overline{Bwd} |
|-----------------|-----------------|------------------|------------------|------------------|------------------|------------------|
| Read | H | H | X | X | X | X |
| Read | H | L | H | H | H | H |
| Write Byte 1 | H | L | L | H | H | H |
| Write All Bytes | H | L | L | L | L | L |
| Write All Bytes | L | X | X | X | X | X |

INTERLEAVED BURST ADDRESS TABLE (MODE = V_{CCQ} or No Connect)

| External Address A1 A0 | 1st Burst Address A1 A0 | 2nd Burst Address A1 A0 | 3rd Burst Address A1 A0 |
|---------------------------|----------------------------|----------------------------|----------------------------|
| 00 | 01 | 10 | 11 |
| 01 | 00 | 11 | 10 |
| 10 | 11 | 00 | 01 |
| 11 | 10 | 01 | 00 |

LINEAR BURST ADDRESS TABLE (MODE = GND_Q)



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

| Symbol | Parameter | Value | Unit |
|------------------------------------|---|--------------------------------|------|
| T _{BIAS} | Temperature Under Bias | -40 to +85 | °C |
| T _{STG} | Storage Temperature | -55 to +150 | °C |
| P _D | Power Dissipation | 1.6 | W |
| I _{OUT} | Output Current (per I/O) | 100 | mA |
| V _{IN} , V _{OUT} | Voltage Relative to GND for I/O Pins | -0.5 to V _{CCQ} + 0.3 | V |
| V _{IN} | Voltage Relative to GND for for Address and Control Inputs | -0.5 to V _{CC} + 0.5 | V |
| V _{CC} | Voltage on V _{CC} Supply Relative to GND | -0.5 to 4.6 | V |

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
3. This device contains circuitry that will ensure the output devices are in High-Z at power up.

OPERATING RANGE

| Range | Ambient Temperature | V _{CC} | V _{CCQ} |
|------------|---------------------|-----------------|------------------|
| Commercial | 0°C to +70°C | 3.3V, +10%, -5% | 2.375–3.6V |
| Industrial | -40°C to +85°C | 3.3V, +10%, -5% | 2.375–3.6V |

DC ELECTRICAL CHARACTERISTICS⁽¹⁾ (Over Operating Range)

| Symbol | Parameter | Test Conditions | Min. | Max. | Unit | |
|-----------------|------------------------|--|------|------------------------|------|----|
| V _{OH} | Output HIGH Voltage | I _{OH} = -2.0 mA, V _{CCQ} = 2.5V | 1.7 | — | V | |
| | | I _{OH} = -4.0 mA, V _{CCQ} = 3.3V | 2.4 | — | V | |
| V _{OL} | Output LOW Voltage | I _{OL} = 2.0 mA, V _{CCQ} = 2.5V | — | 0.7 | V | |
| | | I _{OL} = 8.0 mA, V _{CCQ} = 3.3V | — | 0.4 | V | |
| V _{IH} | Input HIGH Voltage | V _{CCQ} = 2.5V | 1.7 | V _{CCQ} + 0.3 | V | |
| | | V _{CCQ} = 3.3V | 2.0 | V _{CCQ} + 0.3 | V | |
| V _{IL} | Input LOW Voltage | V _{CCQ} = 2.5V | -0.3 | 0.7 | V | |
| | | V _{CCQ} = 3.3V | -0.3 | 0.8 | V | |
| I _{LI} | Input Leakage Current | GND ≤ V _{IN} ≤ V _{CCQ} ⁽²⁾ | Com. | -2 | 2 | μA |
| | | | Ind. | -5 | 5 | |
| I _{LO} | Output Leakage Current | GND ≤ V _{OUT} ≤ V _{CCQ} , $\overline{OE} = V_{IH}$ | Com. | -2 | 2 | μA |
| | | | Ind. | -5 | 5 | |

POWER SUPPLY CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | Test Conditions | -8.5 Max. | -9 Max. | -10 Max. | Unit | |
|-----------------|--------------------------------|---|--------------|------------|-------------|------|----|
| I _{CC} | AC Operating Supply Current | Device Selected, All Inputs = V _{IL} or V _{IH} $\overline{OE} = V_{IH}$, V _{CC} = Max. Cycle Time ≥ t _{kc} min. | Com. | 200 | 175 | 150 | mA |
| | | | Ind. | | 185 | 160 | mA |
| I _{SB} | Standby Current | Device Deselected, V _{CC} = Max., All Inputs = V _{IH} or V _{IL} CLK Cycle Time ≥ t _{kc} min. | Com. | 20 | 20 | 20 | mA |
| | | | Ind. | | 25 | 25 | mA |

Notes:

1. The MODE pin has an internal pullup. This pin may be a No Connect, tied to GND, or tied to V_{CC}.
2. The MODE pin should be tied to V_{CC} or GND. It exhibits ±10 μA maximum leakage current when tied to - GND + 0.2V or ≥ V_{CC} - 0.2V.

CAPACITANCE^(1,2)

| Symbol | Parameter | Conditions | Max. | Unit |
|------------------|--------------------------|-----------------------|------|------|
| C _{IN} | Input Capacitance | V _{IN} = 0V | 6 | pF |
| C _{OUT} | Input/Output Capacitance | V _{OUT} = 0V | 8 | pF |

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V.

AC TEST CONDITIONS

| Parameter | Unit |
|---|---|
| Input Pulse Level | 0V to 3.0V |
| Input Rise and Fall Times | 1.5 ns |
| Input and Output Timing and Reference Level | 1.5V for 3.3V I/O V _{CCQ} /2 for 2.5V I/O |
| Output Load | See Figures 1 and 2 |

AC TEST LOADS

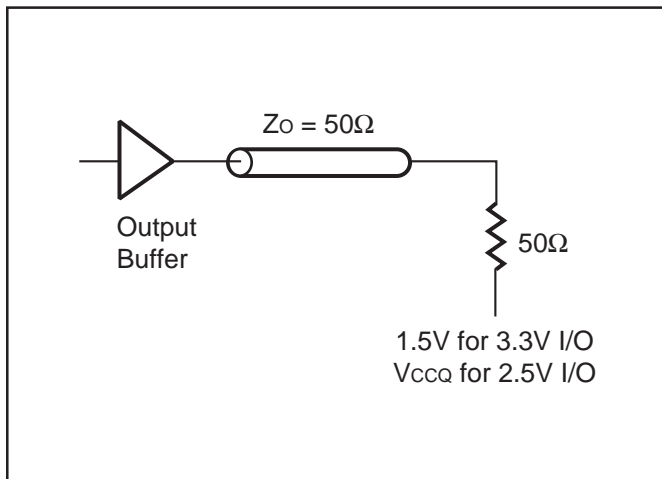


Figure 1

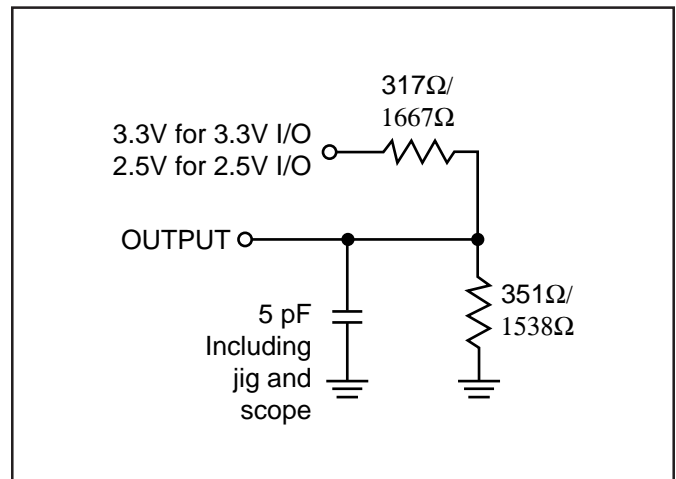


Figure 2

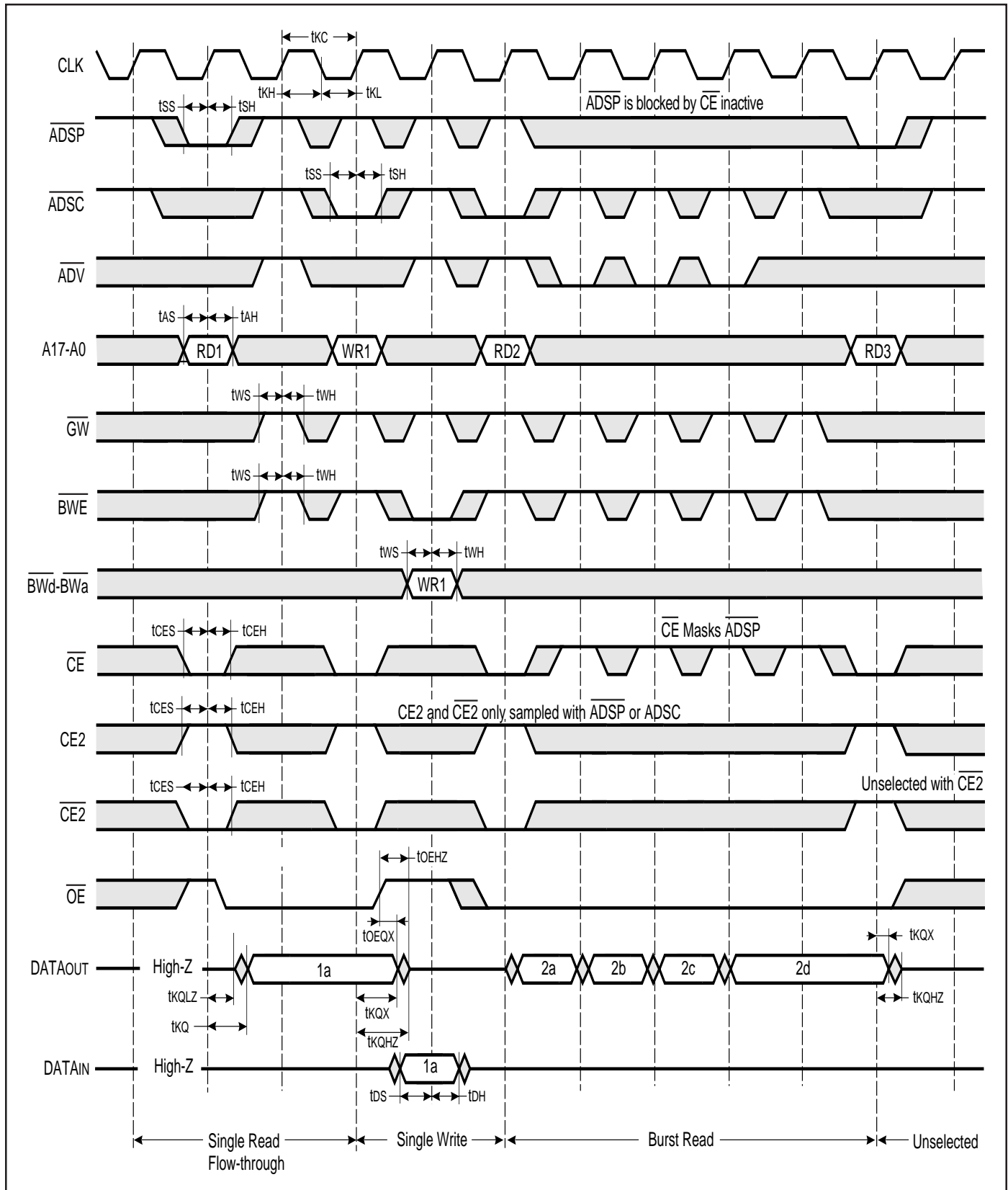
READ/WRITE CYCLE SWITCHING CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | -8.5 | | -9 | | -10 | | Unit |
|------------------------------------|--------------------------------|------|------|------|------|------|------|------|
| | | Min. | Max. | Min. | Max. | Min. | Max. | |
| f _{MAX} | Clock Frequency | — | 90 | — | 66 | — | 66 | MHz |
| t _{KC} | Cycle Time | 10 | — | 15 | — | 15 | — | ns |
| t _{KH} | Clock High Pulse Width | 3.0 | — | 4.0 | — | 4.0 | — | ns |
| t _{KL} | Clock Low Pulse Width | 3.0 | — | 4.0 | — | 4.0 | — | ns |
| t _{KQ} | Clock Access Time | — | 8.5 | — | 9 | — | 10 | ns |
| t _{KQX} ⁽¹⁾ | Clock High to Output Invalid | 2 | — | 2 | — | 2 | — | ns |
| t _{KQLZ} ^(1,2) | Clock High to Output Low-Z | 0 | — | 0 | — | 0 | — | ns |
| t _{KQHZ} ^(1,2) | Clock High to Output High-Z | 2 | 3.8 | 2 | 4 | 1.5 | 4.2 | ns |
| t _{OEQ} | Output Enable to Output Valid | — | 3.8 | — | 4 | — | 5 | ns |
| t _{OELZ} ^(1,2) | Output Enable to Output Low-Z | 0 | — | 0 | — | 0 | — | ns |
| t _{OEHZ} ^(1,2) | Output Enable to Output High-Z | — | 3.8 | — | 4 | — | 5 | ns |
| t _{AS} | Address Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{SS} | Address Status Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{WS} | Write Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{CES} | Chip Enable Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{AVS} | Address Advance Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{AH} | Address Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{SH} | Address Status Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{WH} | Write Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{CEH} | Chip Enable Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{AVH} | Address Advance Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |

Note:

1. Guaranteed but not 100% tested. This parameter is periodically sampled.
2. Tested with load in Figure 2.

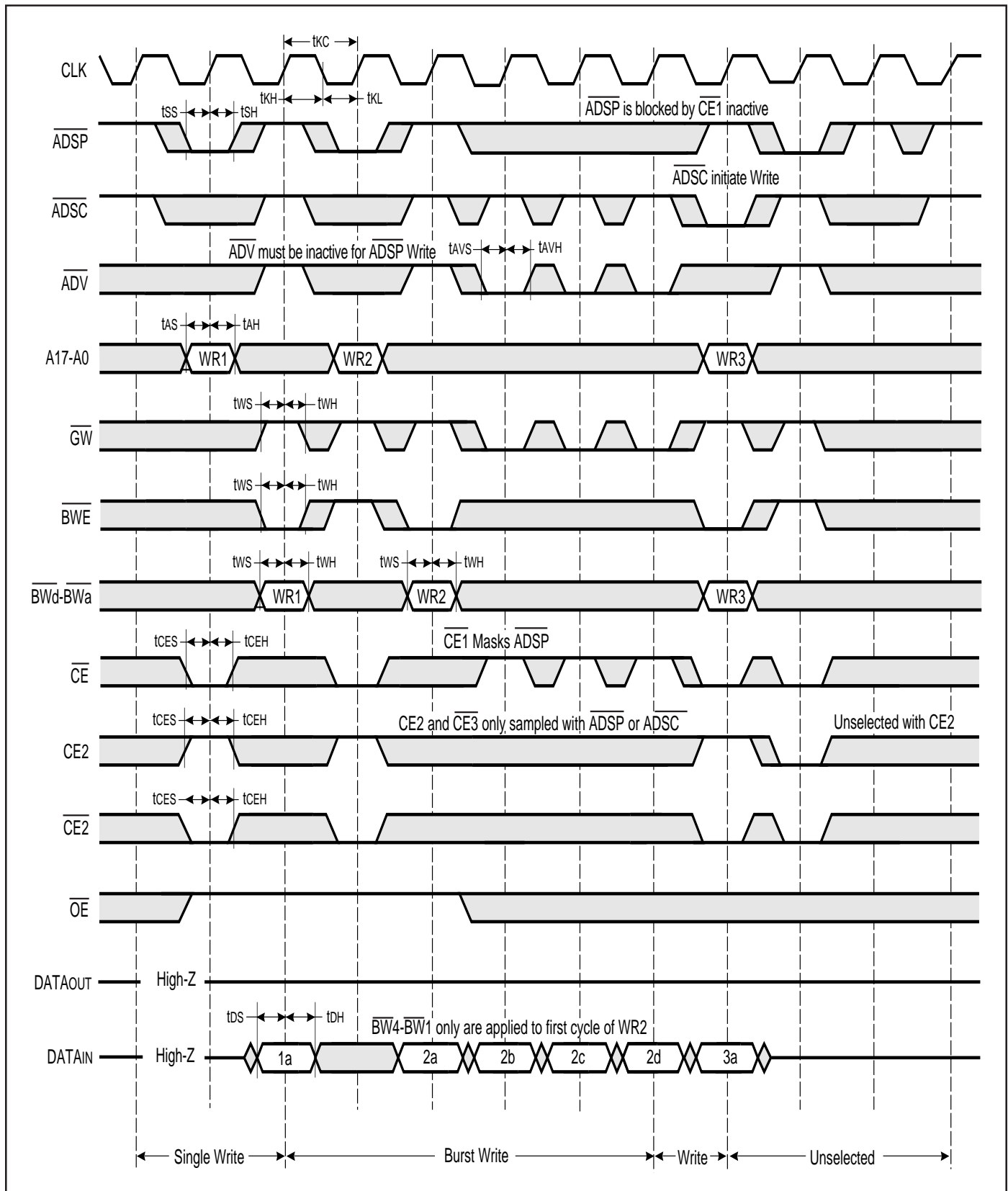
READ/WRITE CYCLE TIMING



WRITE CYCLE SWITCHING CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | -8.5 | | -9 | | -10 | | Unit |
|------------------|----------------------------|------|------|------|------|------|------|------|
| | | Min. | Max. | Min. | Max. | Min. | Max. | |
| t _{KC} | Cycle Time | 10 | — | 15 | — | 15 | — | ns |
| t _{KH} | Clock High Pulse Width | 3.0 | — | 4.0 | — | 4.0 | — | ns |
| t _{KL} | Clock Low Pulse Width | 3.0 | — | 4.0 | — | 4.0 | — | ns |
| t _{AS} | Address Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{SS} | Address Status Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{WS} | Write Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{DS} | Data In Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{CES} | Chip Enable Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{AVS} | Address Advance Setup Time | 1.8 | — | 2 | — | 2 | — | ns |
| t _{AH} | Address Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{SH} | Address Status Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{DH} | Data In Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{WH} | Write Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{CEH} | Chip Enable Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| t _{AVH} | Address Advance Hold Time | 0.5 | — | 0.5 | — | 0.5 | — | ns |

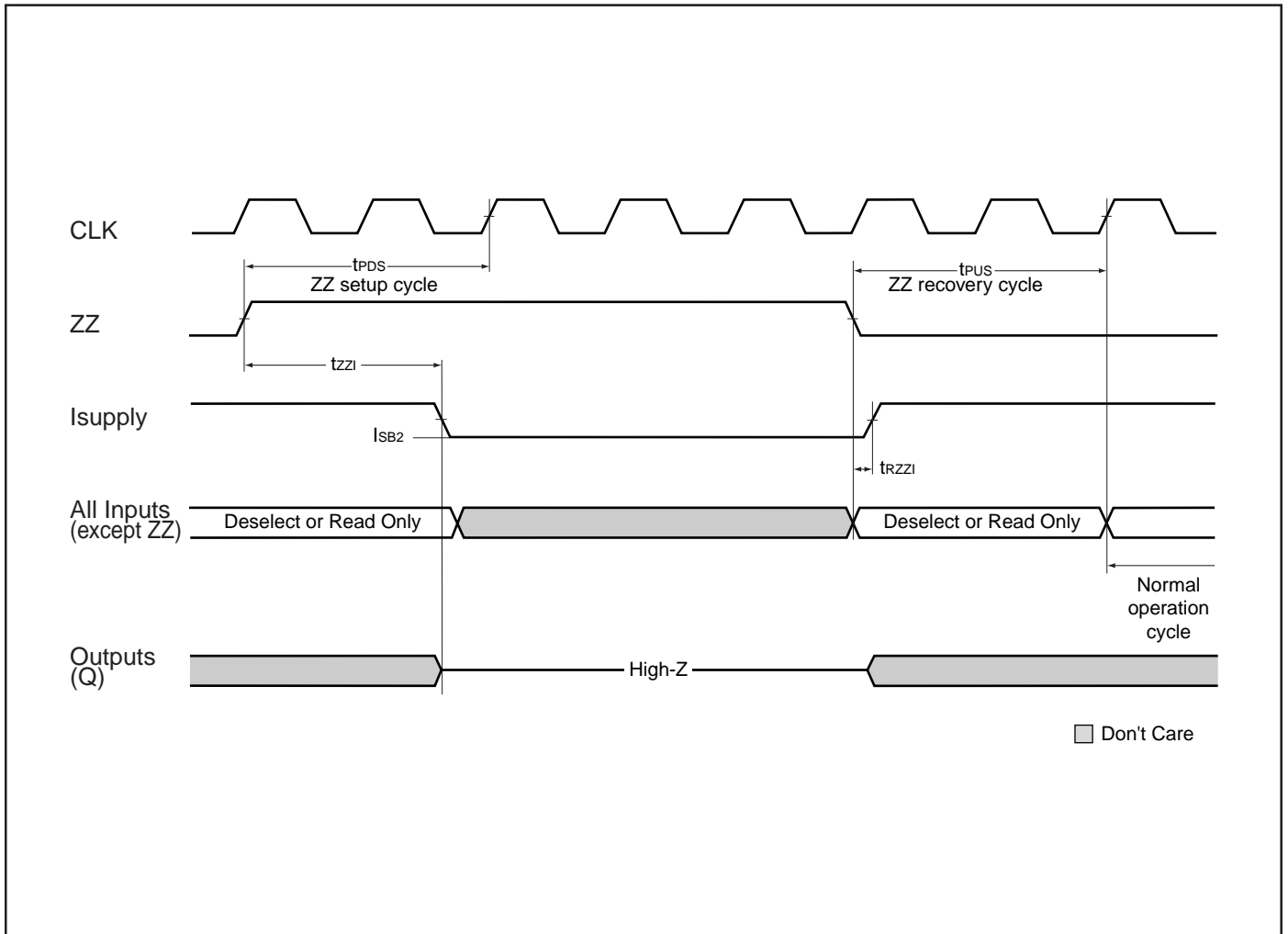
WRITE CYCLE TIMING



SLEEP MODE ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Conditions | Min. | Max. | Unit |
|--------|-----------------------------------|------------|------|------|-------|
| ISB2 | Current during SLEEP MODE | ZZ ≥ Vih | — | 15 | mA |
| tpDS | ZZ active to input ignored | | 2 | — | cycle |
| tpUS | ZZ inactive to input sampled | | 2 | — | cycle |
| tzZI | ZZ active to SLEEP current | | 2 | — | cycle |
| trZZI | ZZ inactive to exit SLEEP current | | 0 | — | ns |

SLEEP MODE TIMING



IS61SF25632T/D IS61LF25632T/D
 IS61SF25636T/D IS61LF25636T/D
 IS61SF51218T/D IS61LF51218T/D



ORDERING INFORMATION

Commercial Range: 0°C to +70°C

| Speed | Order Part Number | Package |
|-------|-------------------|---------|
| 9 ns | IS61SF25632T-9TQ | TQFP |
| | IS61SF25632D-9TQ | TQFP |
| | IS61SF25632D-9B | PBGA |
| 10 ns | IS61SF25632T-10TQ | TQFP |
| | IS61SF25632D-10TQ | TQFP |
| | IS61SF25632D-10B | PBGA |

Commercial Range: 0°C to +70°C

| Speed | Order Part Number | Package |
|-------|-------------------|---------|
| 9 ns | IS61SF25636T-9TQ | TQFP |
| | IS61SF25636D-9TQ | TQFP |
| | IS61SF25636D-9B | PBGA |
| 10 ns | IS61SF25636T-10TQ | TQFP |
| | IS61SF25636D-10TQ | TQFP |
| | IS61SF25636D-10B | PBGA |

Industrial Range: -40°C to +85°C

| Speed | Order Part Number | Package |
|-------|--------------------|---------|
| 9 ns | IS61SF25632T-9TQI | TQFP |
| | IS61SF25632D-9TQI | TQFP |
| 10 ns | IS61SF25632T-10TQI | TQFP |
| | IS61SF25632D-10TQI | TQFP |

Industrial Range: -40°C to +85°C

| Speed | Order Part Number | Package |
|-------|--------------------|---------|
| 9 ns | IS61SF25636T-9TQI | TQFP |
| | IS61SF25636D-9TQI | TQFP |
| 10 ns | IS61SF25636T-10TQI | TQFP |
| | IS61SF25636D-10TQI | TQFP |

IS61SF25632T/D IS61LF25632T/D
IS61SF25636T/D IS61LF25636T/D
IS61SF51218T/D IS61LF51218T/D



ORDERING INFORMATION

Commercial Range: 0°C to +70°C

| Speed | Order Part Number | Package |
|--------|--------------------|---------|
| 8.5 ns | IS61SF51218T-8.5TQ | TQFP |
| | IS61SF51218D-8.5TQ | TQFP |
| | IS61SF51218D-8.5B | PBGA |
| 9 ns | IS61SF51218T-9TQ | TQFP |
| | IS61SF51218D-9TQ | TQFP |
| | IS61SF51218D-9B | PBGA |
| 10 ns | IS61SF51218T-10TQ | TQFP |
| | IS61SF51218D-10TQ | TQFP |
| | IS61SF51218D-10B | PBGA |

Industrial Range: -40°C to +85°C

| Speed | Order Part Number | Package |
|-------|--------------------|---------|
| 9 ns | IS61SF51218T-9TQI | TQFP |
| | IS61SF51218D-9TQI | TQFP |
| 10 ns | IS61SF51218T-10TQI | TQFP |
| | IS61SF51218D-10TQI | TQFP |

IS61SF25632T/D IS61LF25632T/D
 IS61SF25636T/D IS61LF25636T/D
 IS61SF51218T/D IS61LF51218T/D



ORDERING INFORMATION

Commercial Range: 0°C to +70°C

| Speed | Order Part Number | Package |
|-------|-------------------|---------|
| 9 ns | IS61LF25632T-9TQ | TQFP |
| | IS61LF25632D-9TQ | TQFP |
| | IS61LF25632D-9B | PBGA |
| 10 ns | IS61LF25632T-10TQ | TQFP |
| | IS61LF25632D-10TQ | TQFP |
| | IS61LF25632D-10B | PBGA |

Commercial Range: 0°C to +70°C

| Speed | Order Part Number | Package |
|-------|-------------------|---------|
| 9 ns | IS61LF25636T-9TQ | TQFP |
| | IS61LF25636D-9TQ | TQFP |
| | IS61LF25636D-9B | PBGA |
| 10 ns | IS61LF25636T-10TQ | TQFP |
| | IS61LF25636D-10TQ | TQFP |
| | IS61LF25636D-10B | PBGA |

Industrial Range: -40°C to +85°C

| Speed | Order Part Number | Package |
|-------|--------------------|---------|
| 9 ns | IS61LF25632T-9TQI | TQFP |
| | IS61LF25632D-9TQI | TQFP |
| 10 ns | IS61LF25632T-10TQI | TQFP |
| | IS61LF25632D-10TQI | TQFP |

Industrial Range: -40°C to +85°C

| Speed | Order Part Number | Package |
|-------|--------------------|---------|
| 9 ns | IS61LF25636T-9TQI | TQFP |
| | IS61LF25636D-9TQI | TQFP |
| 10 ns | IS61LF25636T-10TQI | TQFP |
| | IS61LF25636D-10TQI | TQFP |

IS61SF25632T/D IS61LF25632T/D
IS61SF25636T/D IS61LF25636T/D
IS61SF51218T/D IS61LF51218T/D



ORDERING INFORMATION

Commercial Range: 0°C to +70°C

| Speed | Order Part Number | Package |
|-------|-------------------|---------|
| 9 ns | IS61LF51218T-9TQ | TQFP |
| | IS61LF51218D-9TQ | TQFP |
| | IS61LF51218D-9B | PBGA |
| 10 ns | IS61LF51218T-10TQ | TQFP |
| | IS61LF51218D-10TQ | TQFP |
| | IS61LF51218D-10B | PBGA |

Industrial Range: -40°C to +85°C

| Speed | Order Part Number | Package |
|-------|--------------------|---------|
| 9 ns | IS61LF51218T-9TQI | TQFP |
| | IS61LF51218D-9TQI | TQFP |
| 10 ns | IS61LF51218T-10TQI | TQFP |
| | IS61LF51218D-10TQI | TQFP |



Integrated Silicon Solution, Inc.

2231 Lawson Lane
Santa Clara, CA 95054
Tel: 1-800-379-4774
Fax: (408) 588-0806
E-mail: sales@issi.com
www.issi.com